Electrical Characteristics at T_j XQOHVV RWKHUZLVH VSHFLILHG

Static Characteristics

Parameter	Symbol	Conditions		Value typ	max	Unit
Drain to Source Breakdown Voltage		V_{GS}=0V, I_D=250 A	80	-	-	
					4	
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS}=0V, V_{DS}=80V, T_j	-	-	1	A
		V_{GS}=0V, V_{DS}=80V, T_j	-	-	100	
Gate to Source Leakage Current	I_{GSS}			-		
Drain to Source on Resistance	$R_{DS(on)}$		-		0.9	m
		V_{GS}=0V, V_{DS} Open, f=1MHz	-	0.64		
				19090	-	
			-	2871		

Fig 1. Typical Output Characteristics

Figure 2. On-Resistance vs. Gate-Source Voltage

Figure 3. On-Resistance vs. Drain Current and Gate Voltage

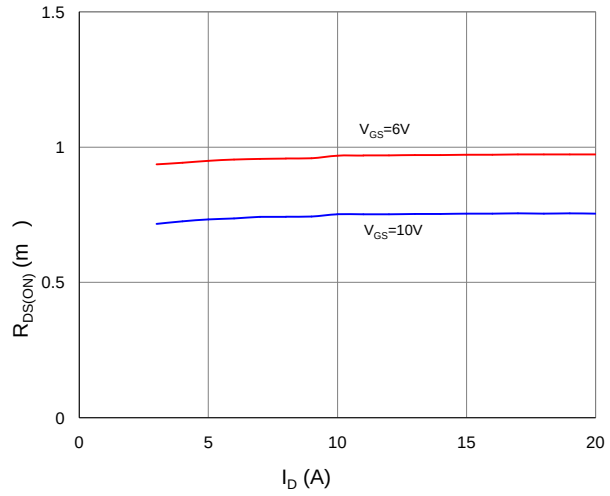


Figure 4. Normalized On-Resistance vs. Junction Temperature

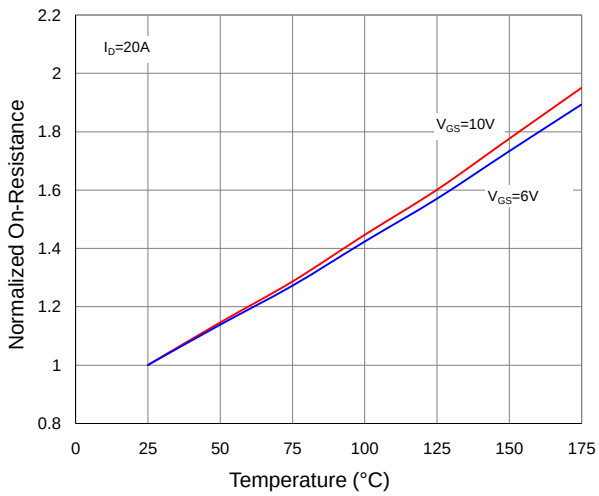


Figure 5. Typical Transfer Characteristics

Figure 6. Typical Source-Drain Diode Forward Voltage

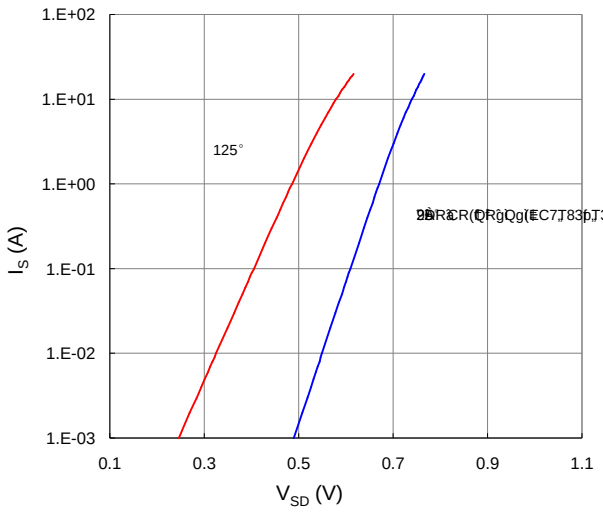


Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage

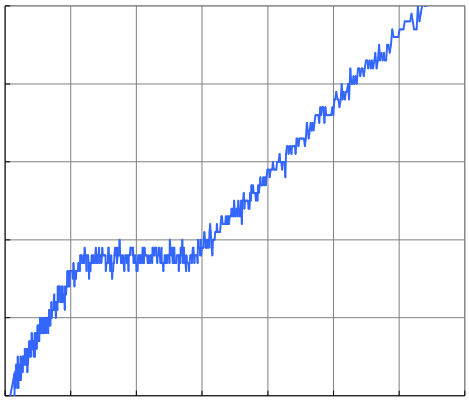


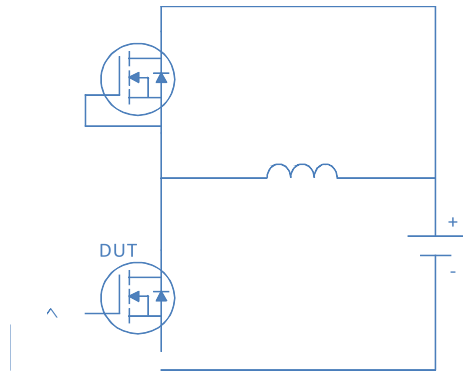
Figure 8. Typical Capacitance vs. Drain-to-Source Voltage

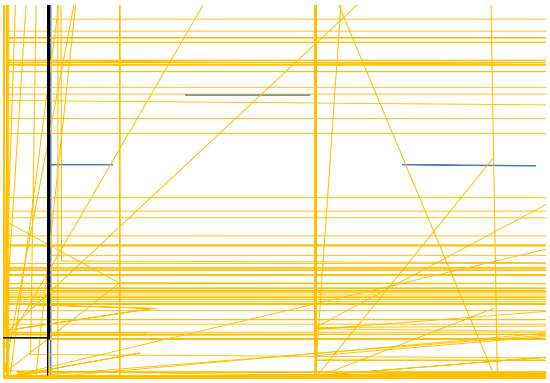
Figure 9. Maximum Safe Operating Area

Figure 10. Maximun Drain Current vs. Case Temperature

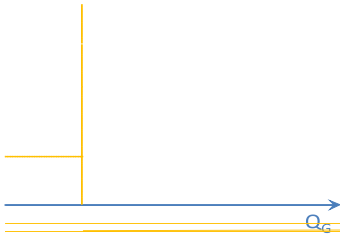
Figure 11. Normalized Maximum Transient Thermal Impedance, Junction-to-Case

Inductive switching Test

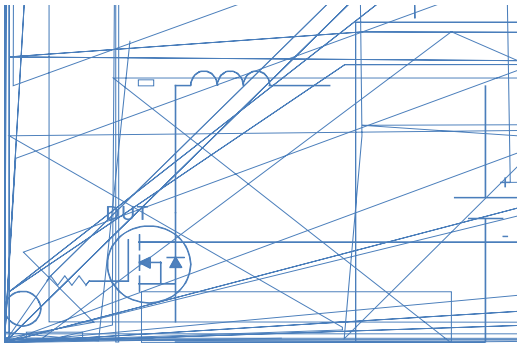


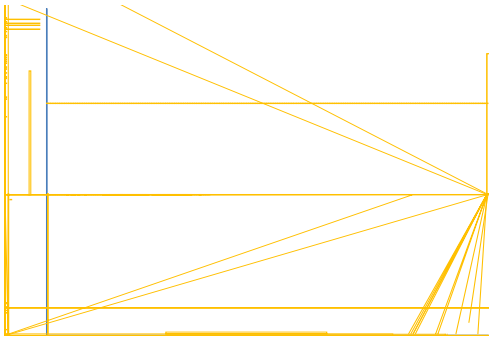


Gate Charge Test

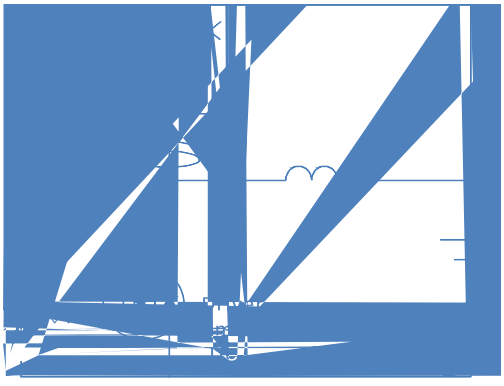


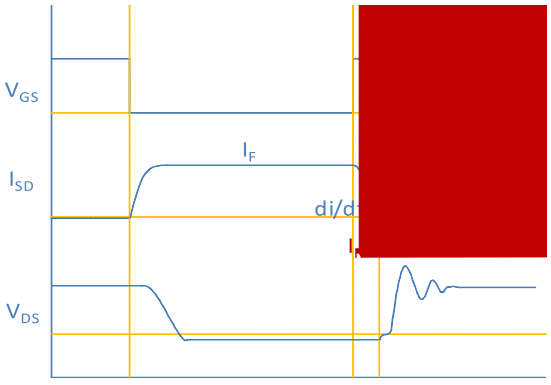
Uclamped Inductive Switching (UIS) Test



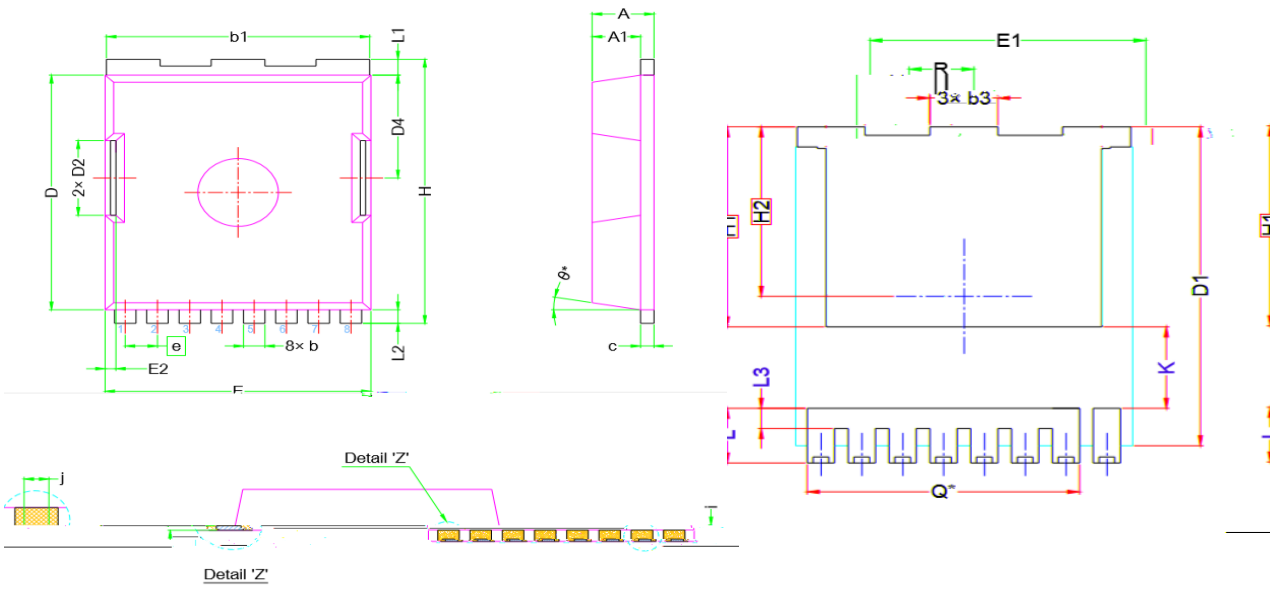
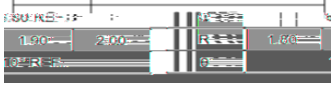


Diode Recovery Test





TOLL, 8 leads



SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	2.20	2.30	2.40
A1	1.70	1.80	1.90
b	0.70	0.80	0.90
b1	9.70	9.80	9.90
b3	1.90	2.00	2.10
c	0.40	0.50	0.60
D	10.28	10.38	10.48
D1	10.98	11.08	11.18
D2	3.20	3.30	3.40
D4	4.45	4.55	4.65
E	9.80	9.90	10.00
E1	8.00	8.10	8.20
E2	0.30	0.40	0.50
e	1.20 BSC		
H	11.58	11.68	11.78
H1	6.95 BSC		
H2	5.89 BSC		
i	0.10 REF.		
j	0.46 REF.		
K	2.80 REF.		
L	1.60	1.90	2.10
L1	0.60	0.70	0.80
L2	0.50	0.60	0.70
L3	0.60	0.70	0.80
N	8